TEXAS INSTRUMENTS

Data sheet acquired from Harris Semiconductor
SCHS192B

January 1998 - Revised May 2003

CD54HC640, CD74HC640, CD54HCT640, CD74HCT640

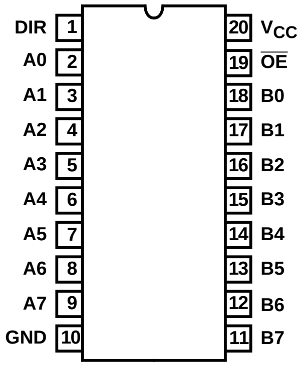
High-Speed CMOS Logic Octal Three-State Bus Transceiver, Inverting

Features

- **Buffered Inputs**
- **Three-State Outputs**
- **Applications in Multiple-Data-Bus Architecture**
- **Fanout (Over Temperature Range)**
  - **Standard Outputs . . . . 10 LSTTL Loads**
  - **Bus Driver Outputs . . . . 15 LSTTL Loads**
- **Wide Operating Temperature Range . . . -55^{o}C to 125^{o}C**
- **Balanced Propagation Delay and Transition Times**
- **Significant Power Reduction Compared to LSTTL Logic ICs**
- **HC Types**
  - **2V to 6V Operation**
  - **High Noise Immunity: N_{IL} = 30%, N_{IH} = 30% of V_{CC} at V_{CC} = 5V**
- **HCT Types**
  - **4.5V to 5.5V Operation**
  - **Direct LSTTL Input Logic Compatibility, V_{IL}= 0.8V (Max), V_{IH} = 2V (Min)**
  - **CMOS Input Compatibility, $I_I \le 1\mu A$ at V_{OL}, V_{OH}**

Pinout

CD54HC640, CD54HCT640
(CERDIP)
CD74HC640, CD74HCT640
(PDIP, SOIC)
TOP VIEW



Description

The ’HC640 and ’HCT640 silicon-gate CMOS three-state bidirectional inverting and non-inverting buffers are intended for two-way asynchronous communication between data buses. They have high drive current outputs which enable high-speed operation when driving large bus capacitances. These circuits possess the low power dissipation of CMOS circuits, and have speeds comparable to low power Schottky TTL circuits. They can drive 15 LSTTL loads. The ’HC640 and ’HCT640 are inverting buffers.

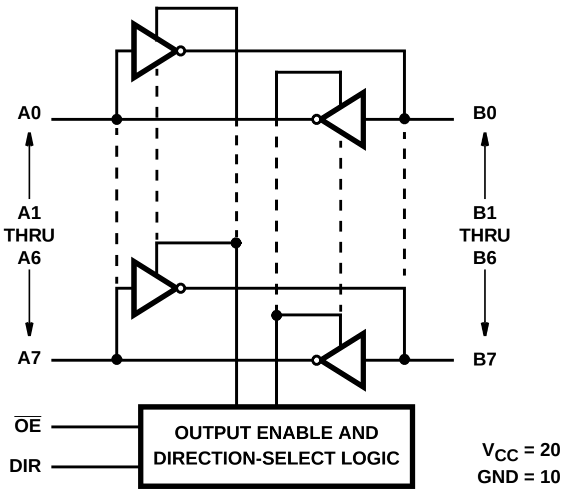
The direction of data flow (A to B, B to A) is controlled by the DIR input.

Outputs are enabled by a low on the Output Enable input ($\overline{OE}$); a high $\overline{OE}$ puts these devices in the high impedance mode.

Ordering Information

PART NUMBER	TEMP. RANGE (^{o}C)	PACKAGE
CD54HC640F3A	-55 to 125	20 Ld CERDIP
CD54HCT640F3A	-55 to 125	20 Ld CERDIP
CD74HC640E	-55 to 125	20 Ld PDIP
CD74HC640M	-55 to 125	20 Ld SOIC
CD74HCT640E	-55 to 125	20 Ld PDIP
CD74HCT640M	-55 to 125	20 Ld SOIC

Functional Diagram



TRUTH TABLE

CONTROL INPUTS		DATA PORT STATUS	
$\overline{OE}$	DIR	A_n	B_n
L	L	$\overline{O}$	I
H	H	Z	Z
H	L	Z	Z
L	H	I	$\overline{O}$

To prevent excess currents in the High-Z modes all I/O terminals should be terminated with 1kΩ to 1MΩ resistors.
H = High Level
L = Low Level
I = Input
$\overline{O}$ = Output (Inversion of Input Level)
Z = High Impedance

Absolute Maximum Ratings

DC Supply Voltage, V_{CC} . . . . -0.5V to 7V
DC Input Diode Current, I_{IK}
  For $V_I < -0.5V$ or $V_I > V_{CC} + 0.5V$ . . . .±20mA
DC Output Diode Current, I_{OK}
  For $V_O < -0.5V$ or $V_O > V_{CC} + 0.5V$ . . . .±20mA
DC Drain Current, per Output, I_O
  For $-0.5V < V_O < V_{CC} + 0.5V$ . . . .±35mA
DC Output Source or Sink Current per Output Pin, I_O
  For $V_O > -0.5V$ or $V_O < V_{CC} + 0.5V$ . . . .±25mA
DC V_{CC} or Ground Current, I_{CC} . . . .±50mA

Operating Conditions

Temperature Range, T_A . . . . -55^{o}C to 125^{o}C
Supply Voltage Range, V_{CC}
  HC Types . . . . .2V to 6V
  HCT Types . . . . .4.5V to 5.5V
DC Input or Output Voltage, V_I, V_O . . . . 0V to V_{CC}
Input Rise and Fall Time
  2V . . . . 1000ns (Max)
  4.5V. . . . . 500ns (Max)
  6V . . . . 400ns (Max)

Thermal Information

Thermal Resistance (Typical, Note 1)	θ_{JA} (^{o}C/W)
E (PDIP) Package	69
M (SOIC) Package.	58

Maximum Junction Temperature . . . . 150^{o}C
Maximum Storage Temperature Range . . . .-65^{o}C to 150^{o}C
Maximum Lead Temperature (Soldering 10s) . . . . 300^{o}C
  (SOIC - Lead Tips Only)

CAUTION: Stresses above those indicated in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

NOTE:

1. The package thermal impedance is calculated in accordance with JESD 51-7.

DC Electrical Specifications

		TEST CONDITIONS			25^{o}C			-40^{o}C TO 85^{o}C		-55^{o}C TO 125^{o}C		
PARAMETER	SYMBOL	V_I (V)	I_O (mA)	V_{CC} (V)	MIN	TYP	MAX	MIN	MAX	MIN	MAX	UNITS
HC TYPES												
High Level Input Voltage	V_{IH}	-	-	2	1.5	-	-	1.5	-	1.5	-	V
				4.5	3.15	-	-	3.15	-	3.15	-	V
				6	4.2	-	-	4.2	-	4.2	-	V
Low Level Input Voltage	V_{IL}	-	-	2	-	-	0.5	-	0.5	-	0.5	V
				4.5	-	-	1.35	-	1.35	-	1.35	V
				6	-	-	1.8	-	1.8	-	1.8	V
High Level Output Voltage CMOS Loads	V_{OH}	V_{IH} or V_{IL}	-0.02	2	1.9	-	-	1.9	-	1.9	-	V
			-0.02	4.5	4.4	-	-	4.4	-	4.4	-	V
			-0.02	6	5.9	-	-	5.9	-	5.9	-	V
High Level Output Voltage TTL Loads			-	-	-	-	-	-	-	-	-	V
			-6	4.5	3.98	-	-	3.84	-	3.7	-	V
			-7.8	6	5.48	-	-	5.34	-	5.2	-	V
Low Level Output Voltage CMOS Loads	V_{OL}	V_{IH} or V_{IL}	0.02	2	-	-	0.1	-	0.1	-	0.1	V
			0.02	4.5	-	-	0.1	-	0.1	-	0.1	V
			0.02	6	-	-	0.1	-	0.1	-	0.1	V
Low Level Output Voltage TTL Loads			-	-	-	-	-	-	-	-	-	V
			6	4.5	-	-	0.26	-	0.33	-	0.4	V
			7.8	6	-	-	0.26	-	0.33	-	0.4	V
Input Leakage Current	I_I	V_{CC} or GND	-	6	-	-	±0.1	-	±1	-	±1	µA

DC Electrical Specifications **(Continued)**

PARAMETER	SYMBOL	TEST CONDITIONS		V_{CC} (V)	25°C			-40°C TO 85°C		-55°C TO 125°C		UNITS
		V_I (V)	I_O (mA)		MIN	TYP	MAX	MIN	MAX	MIN	MAX	
Quiescent Device Current	I_{CC}	V_{CC} or GND	0	6	-	-	8	-	80	-	160	µA
Three-State Leakage Current	I_{OZ}	V_{IL} or V_{IH}	V_O = V_{CC} or GND	6	-	-	±0.5	-	±5	-	±10	µA
HCT TYPES												
High Level Input Voltage	V_{IH}	-	-	4.5 to 5.5	2	-	-	2	-	2	-	V
Low Level Input Voltage	V_{IL}	-	-	4.5 to 5.5	-	-	0.8	-	0.8	-	0.8	V
High Level Output Voltage CMOS Loads	V_{OH}	V_{IH} or V_{IL}	-0.02	4.5	4.4	-	-	4.4	-	4.4	-	V
High Level Output Voltage TTL Loads			-6	4.5	3.98	-	-	3.84	-	3.7	-	V
Low Level Output Voltage CMOS Loads	V_{OL}	V_{IH} or V_{IL}	0.02	4.5	-	-	0.1	-	0.1	-	0.1	V
Low Level Output Voltage TTL Loads			6	4.5	-	-	0.26	-	0.33	-	0.4	V
Input Leakage Current	I_I	V_{CC} and GND	0	5.5	-	-	±0.1	-	±1	-	±1	µA
Quiescent Device Current	I_{CC}	V_{CC} or GND	0	5.5	-	-	8	-	80	-	160	µA
Three-State Leakage Current	I_{OZ}	V_{IL} or V_{IH}	V_O = V_{CC} or GND	5.5	-	-	±0.5	-	±5	-	±10	µA
Additional Quiescent Device Current Per Input Pin: 1 Unit Load	ΔI_{CC} (Note 2)	V_{CC} -2.1	-	4.5 to 5.5	-	100	360	-	450	-	490	µA

NOTE:

2. For dual-supply systems theoretical worst case (V_I = 2.4V, V_{CC} = 5.5V) specification is 1.8mA.

HCT Input Loading Table

INPUT	UNIT LOADS
DIR	0.9
$\overline{\text{OE}}$, A	1.5
B	1.5

NOTE: Unit Load is ΔI_{CC} limit specified in DC Electrical Table, e.g., 360µA max at 25°C.

Switching Specifications C_L = 50pF, Input t_r, t_f = 6ns

PARAMETER	SYMBOL	TEST CONDITIONS	V_{CC} (V)	25°C			-40°C TO 85°C		-55°C TO 125°C		UNITS
				MIN	TYP	MAX	MIN	MAX	MIN	MAX	
HC TYPES											
Propagation Delay A to $\overline{B}$ B to $\overline{A}$	t_{PHL}, t_{PLH}	C_L = 50pF	2	-	-	90	-	115	-	135	ns
			4.5	-	-	18	-	23	-	27	ns
		C_L = 15pF	5	-	7	-	-	-	-	-	ns
		C_L = 50pF	6	-	-	15	-	20	-	23	ns
Output High-Z To High Level, To Low Level	t_{PHL}, t_{PLH}	C_L = 50pF	2	-	-	150	-	190	-	225	ns
			4.5	-	-	30	-	38	-	45	ns
		C_L = 15pF	5	-	12	-	-	-	-	-	ns
		C_L = 50pF	6	-	-	26	-	33	-	38	ns
Output High Level Output Low Level to High Z	t_{PHZ}, t_{PLZ}	C_L = 50pF	2	-	-	150	-	190	-	225	ns
			4.5	-	-	30	-	38	-	45	ns
		C_L = 15pF	5	-	12	-	-	-	-	-	ns
		C_L = 50pF	6	-	-	26	-	33	-	38	ns
Output Transition Time	t_{THL}, t_{TLH}	C_L = 50pF	2	-	-	60	-	75	-	90	ns
			4.5	-	-	12	-	15	-	18	ns
			6	-	-	10	-	13	-	15	ns
Input Capacitance	C_{IN}	C_L = 50pF	-	10	-	10	-	10	-	10	pF
Three-State Output Capacitance	C_O	-	-	-	-	20	-	20	-	20	pF
Power Dissipation Capacitance (Notes 3, 4)	C_{PD}	-	5	-	38	-	-	-	-	-	pF
HCT TYPES											
Propagation Delay A to $\overline{B}$ B to $\overline{A}$	t_{PHL}, t_{PLH}	C_L = 50pF	4.5	-	-	22	-	28	-	33	ns
		C_L = 15pF	5	-	9	-	-	-	-	-	ns
Output High-Z To High Level, To Low Level	t_{PHL}, t_{PLH}	C_L = 50pF	4.5	-	-	30	-	38	-	45	ns
		C_L = 15pF	5	-	12	-	-	-	-	-	ns
Output High Level Output Low Level to High Z	t_{PHZ}, t_{PLZ}	C_L = 50pF	4.5	-	-	30	-	38	-	45	ns
		C_L = 15pF	5	-	12	-	-	-	-	-	ns
Output Transition Time	t_{THL}, t_{TLH}	C_L = 50pF	4.5	-	-	12	-	15	-	18	ns
Input Capacitance	C_{IN}	C_L = 50pF	-	10	-	10	-	10	-	10	pF
Three-State Output Capacitance	C_O	-	-	-	-	20	-	20	-	20	pF
Power Dissipation Capacitance (Notes 3, 4)	C_{PD}	-	5	-	41	-	-	-	-	-	pF

NOTES:

3. C_{PD} is used to determine the dynamic power consumption, per channel.
4. $P_D = V_{CC}^2 f_i (C_{PD} + C_L)$ where f_i = Input Frequency, C_L = Output Load Capacitance, V_{CC} = Supply Voltage.

Test Circuits and Waveforms

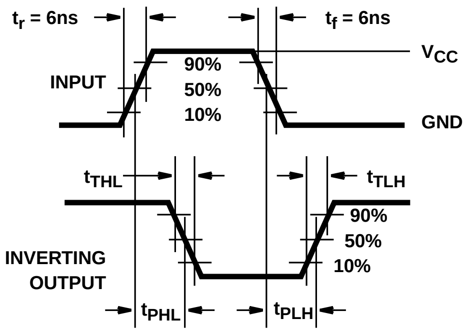


FIGURE 7. HC TRANSITION TIMES AND PROPAGATION DELAY TIMES, COMBINATION LOGIC

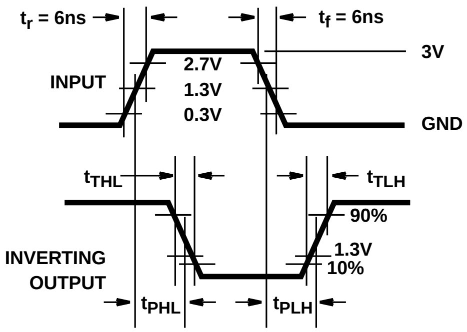


FIGURE 8. HCT TRANSITION TIMES AND PROPAGATION DELAY TIMES, COMBINATION LOGIC

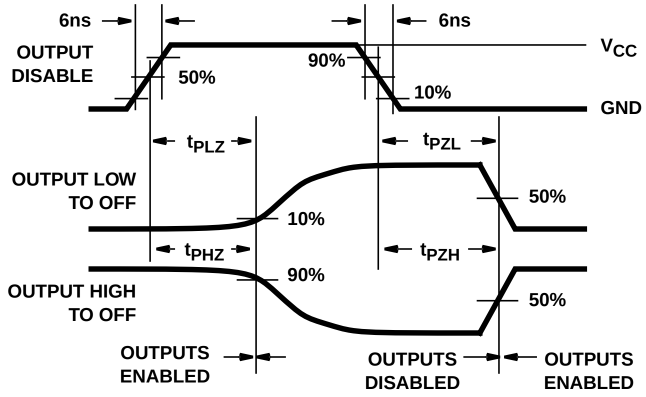


FIGURE 9. HC THREE-STATE PROPAGATION DELAY WAVEFORM

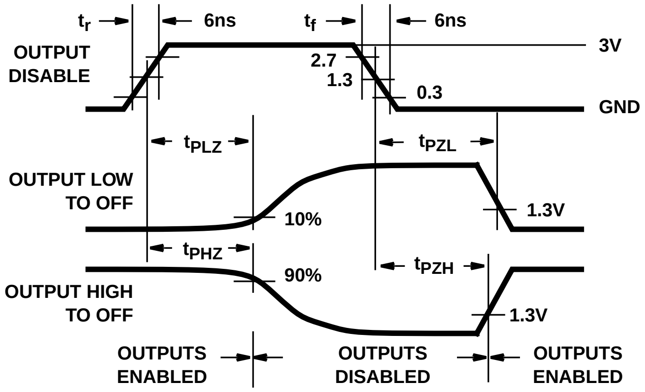
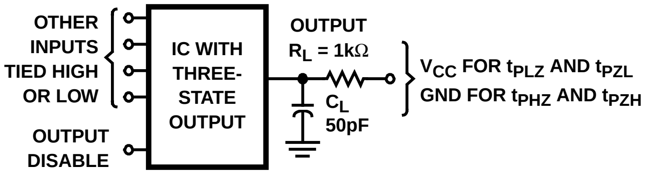


FIGURE 10. HCT THREE-STATE PROPAGATION DELAY WAVEFORM

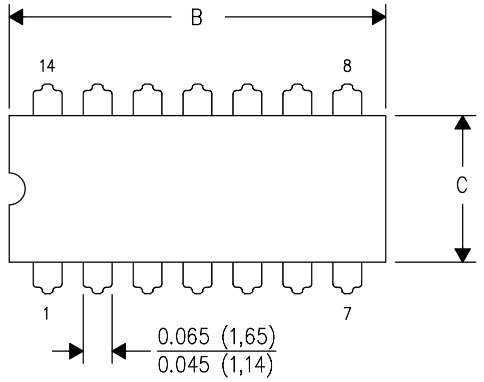


NOTE: Open drain waveforms t_{PLZ} and t_{PZL} are the same as those for three-state shown on the left. The test circuit is Output R_L = 1kΩ to V_{CC}, C_L = 50pF.

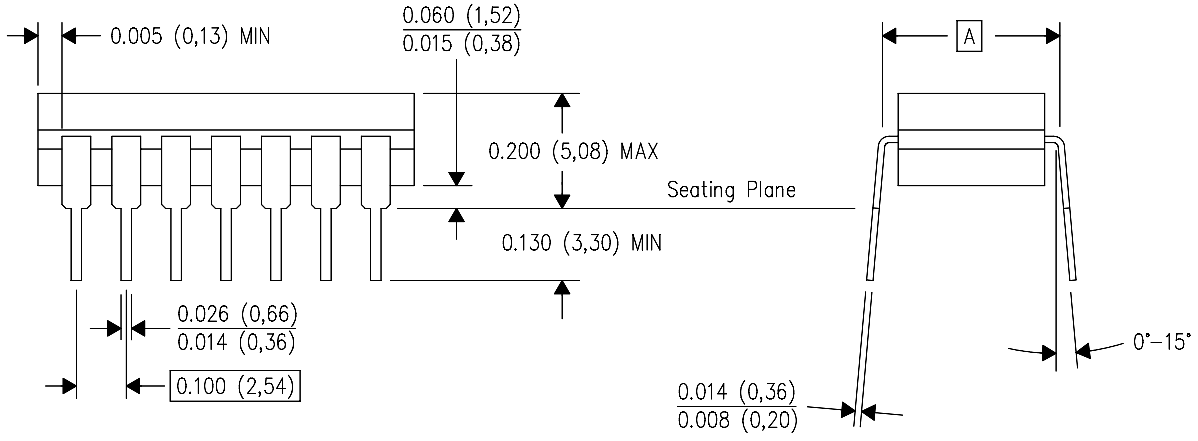
FIGURE 11. HC AND HCT THREE-STATE PROPAGATION DELAY TEST CIRCUIT

J (R–GDIP–T**) CERAMIC DUAL IN–LINE PACKAGE

14 LEADS SHOWN



PINS ** DIM	14	16	18	20
A	0.300 (7,62) BSC	0.300 (7,62) BSC	0.300 (7,62) BSC	0.300 (7,62) BSC
B MAX	0.785 (19,94)	.840 (21,34)	0.960 (24,38)	1.060 (26,92)
B MIN	——	——	——	——
C MAX	0.300 (7,62)	0.300 (7,62)	0.310 (7,87)	0.300 (7,62)
C MIN	0.245 (6,22)	0.245 (6,22)	0.220 (5,59)	0.245 (6,22)

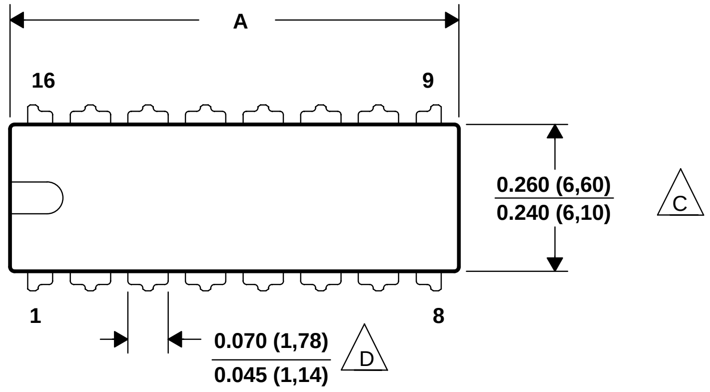


4040083/F 03/03

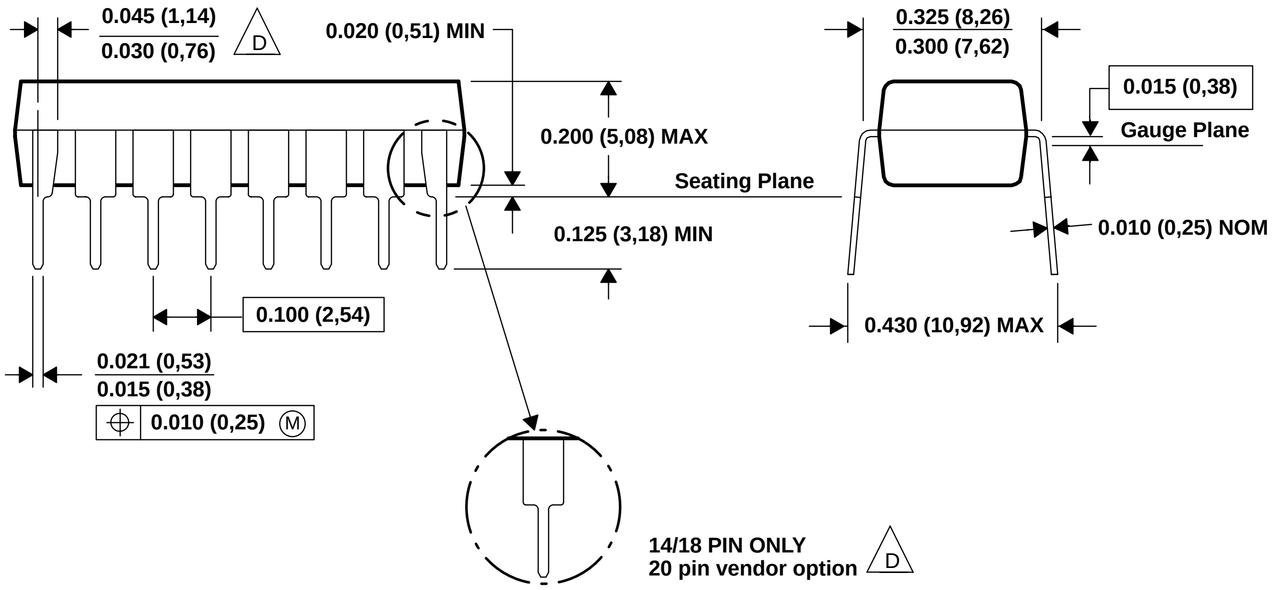
NOTES:
- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- C. This package is hermetically sealed with a ceramic lid using glass frit.
- D. Index point is provided on cap for terminal identification only on press ceramic glass frit seal only.
- E. Falls within MIL STD 1835 GDIP1–T14, GDIP1–T16, GDIP1–T18 and GDIP1–T20.

N (R-PDIP-T**) PLASTIC DUAL-IN-LINE PACKAGE

16 PINS SHOWN



PINS ** / DIM	14	16	18	20
A MAX	0.775 (19,69)	0.775 (19,69)	0.920 (23,37)	1.060 (26,92)
A MIN	0.745 (18,92)	0.745 (18,92)	0.850 (21,59)	0.940 (23,88)
C MS-100 VARIATION	AA	BB	AC	AD

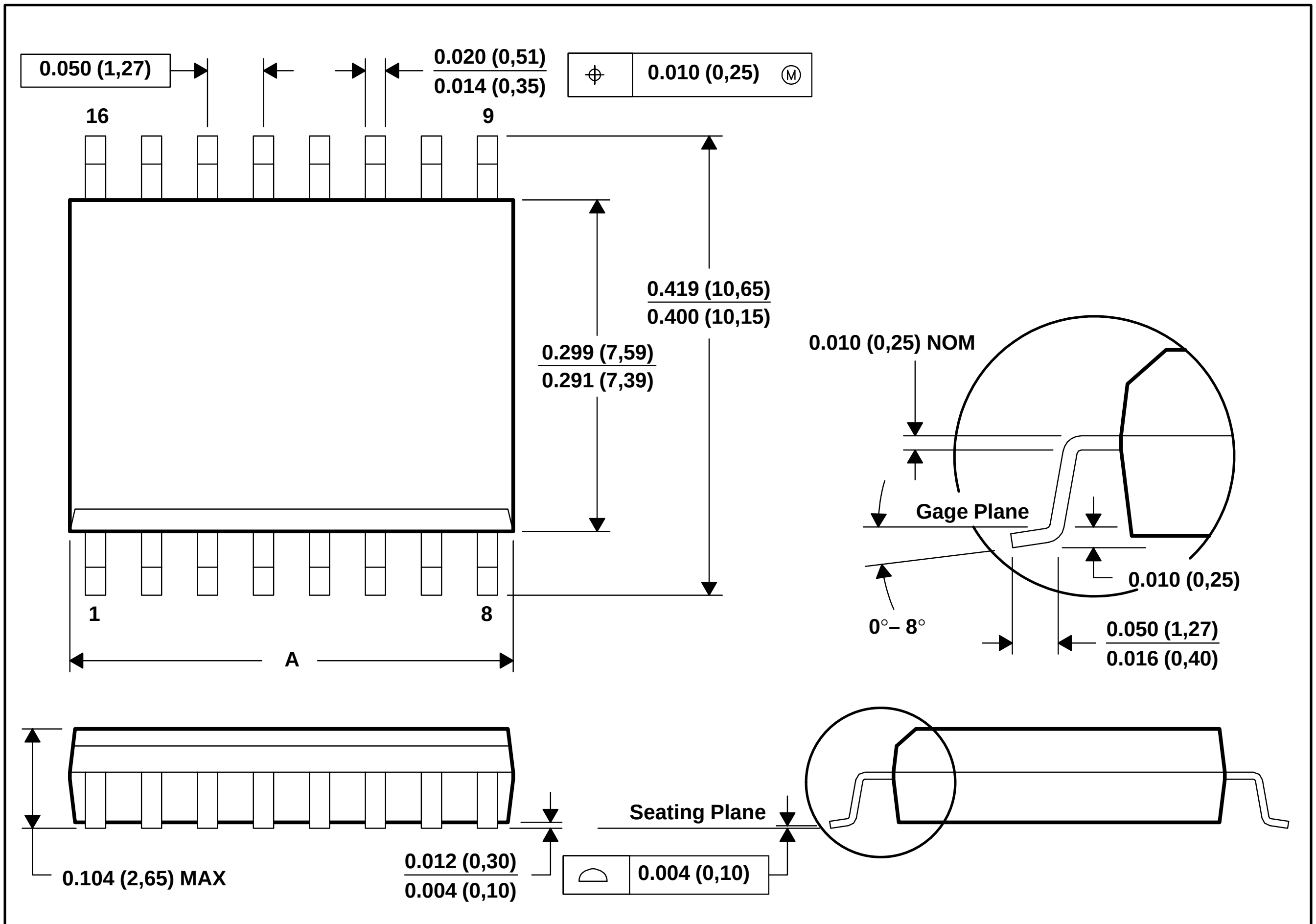


4040049/E 12/2002

NOTES:
- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- C. Falls within JEDEC MS-001, except 18 and 20 pin minimum body lrngth (Dim A).
- D. The 20 pin end lead shoulder width is a vendor option, either half or full width.

DW (R-PDSO-G**) PLASTIC SMALL-OUTLINE PACKAGE

16 PINS SHOWN



PINS ** / DIM	16	18	20	24	28
A MAX	0.410 (10,41)	0.462 (11,73)	0.510 (12,95)	0.610 (15,49)	0.710 (18,03)
A MIN	0.400 (10,16)	0.453 (11,51)	0.500 (12,70)	0.600 (15,24)	0.700 (17,78)

4040000/E 08/01

NOTES:
- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion not to exceed 0.006 (0,15).
- D. Falls within JEDEC MS-013

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